

MMBT5401LT1

Preferred Device

High Voltage Transistor

PNP Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–150	Vdc
Collector–Base Voltage	V_{CBO}	–160	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–500	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

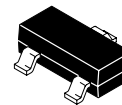
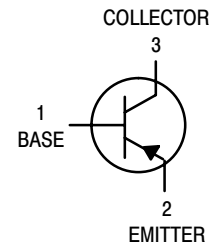
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

- FR–5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

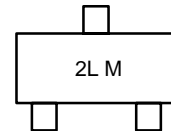


ON Semiconductor®



SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



2L = Device Code
M = Month Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5401LT1	SOT–23	3000 Tape & Reel
MMBT5401LT1G	SOT–23 (Pb–Free)	3000 Tape & Reel
MMBT5401LT3	SOT–23	10,000 Tape & Reel
MMBT5401LT3G	SOT–23 (Pb–Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBT5401LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = –1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	–150	–	Vdc
Collector–Base Breakdown Voltage (I _C = –100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	–160	–	Vdc
Emitter–Base Breakdown Voltage (I _E = –10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	–5.0	–	Vdc
Collector Cutoff Current (V _{CB} = –120 Vdc, I _E = 0) (V _{CB} = –120 Vdc, I _E = 0, T _A = 100°C)	I _{CES}	–	–50	nA _{dc} μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –5.0 Vdc) (I _C = –10 mA _{dc} , V _{CE} = –5.0 Vdc) (I _C = –50 mA _{dc} , V _{CE} = –5.0 Vdc)	h _{FE}	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{CE(sat)}	– –	–0.2 –0.5	Vdc
Base–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{BE(sat)}	– –	–1.0 –1.0	Vdc

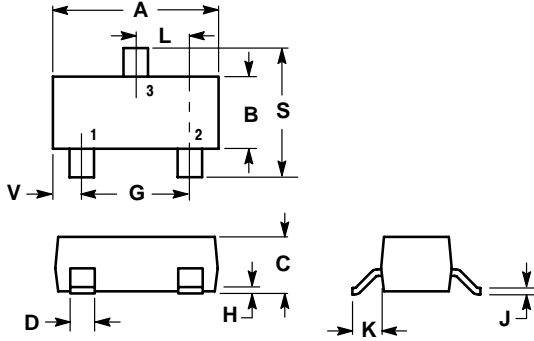
SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = –10 mA _{dc} , V _{CE} = –10 Vdc, f = 100 MHz)	f _T	100	300	MHz
Output Capacitance (V _{CB} = –10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	–	6.0	pF
Small Signal Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –10 Vdc, f = 1.0 kHz)	h _{fe}	40	200	–
Noise Figure (I _C = –200 μA _{dc} , V _{CE} = –5.0 Vdc, R _S = 10 Ω, f = 1.0 kHz)	NF	–	8.0	dB

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PACKAGE DIMENSIONS

SOT-23-3 (TO-236)
CASE 318-08
ISSUE AK

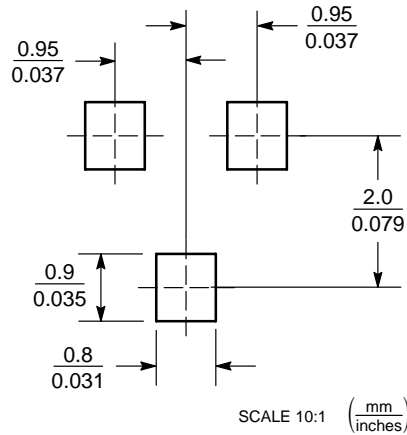


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.